

LSDB3

SILICON BIDIRECTIONAL DIAC

Features

- Breakover Voltage: 32V
- Breakover Voltage Range: 28V to 36V

Maximum Ratings

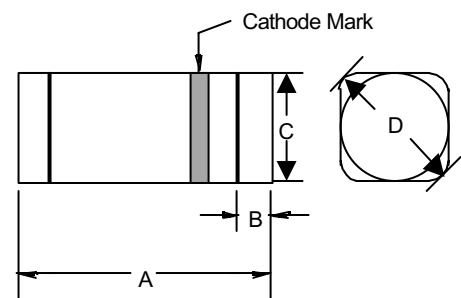
- Operating Junction Temperature: -40°C to +125°C
- Storage Temperature: -40°C to +125°C

Electrical Characteristics @ 25°C Unless Otherwise Specified

Power dissipation on Printed Circuit(I=10mm)	P _C	150mW	T _A =50°C
Repetitive Peak on-state Current	I _{TRM}	2.0A	t _p =20us,f=120Hz
Breakover Voltage	V _{BO}	Min Typ Max 28 32 36V	C=22nF(Note 2)
Breakover Voltage Symmetry	+V _{BO}	±3V	C=22nF(Note 2)
Output Voltage(Note 1)	V _{o(min)}	5V	
Breakover Current(Note 1)	I _{BO(max)}	50uA	C=22nF
Rise Time(Note 1)	T _r	2.0us	
Leakage Current(Note 1)	I _{B(max)}	10uA	V _B =0.5V _{BO(max)}

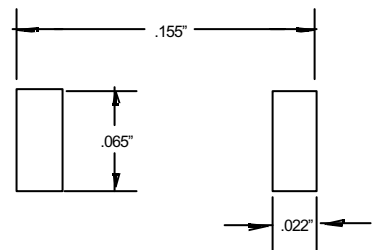
NOTES:1.Electrical characteristics applicable in both forward and reverse directions.
2.Connected in parallel with the devices.

Quadro MELF



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.130	.146	3.30	3.70	
B	.008	.016	.20	.40	
C	.055	.063	1.40	1.60	∅
D	.067		1.70		

SUGGESTED SOLDER PAD LAYOUT



LSDB3

TM

Fig. 1: Relative variation of VBO versus junction temperature (typical values)

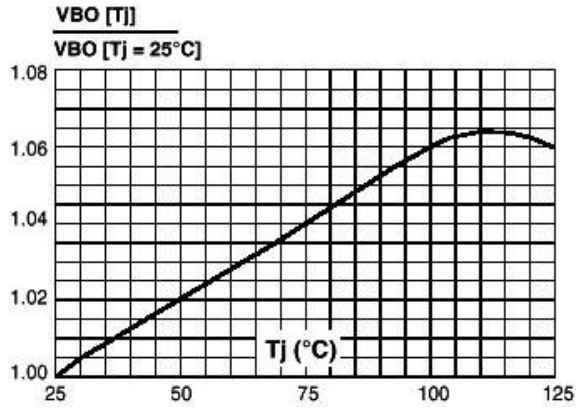


Fig. 2: Repetitive peak pulse current versus pulse duration (maximum values).

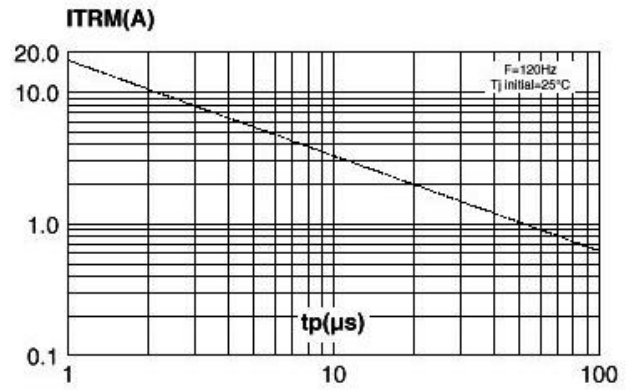


Fig. 3: Time duration while current pulse is higher 50mA versus C and R_s (typical values).

